

a layer of a second conductive material disposed over the first line, the second conductive

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material being different from the first conductive material;

a layer of chalcogenide material disposed over the layer of the second conductive

material; and

a second line formed over the layer of chalcogenide material.

16 17. (Once Amended) The memory cell, as set forth in claim *16*, wherein the first line

is embedded in the substrate.

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17 18. (Once Amended) The memory cell, as set forth in claim *16*, wherein the first line

is disposed in a window formed in a dielectric layer disposed over the substrate.

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(Once Amended) The memory cell, as set forth in claim *16*, wherein the layer of silver is deposited on the first line using an immersion plating technique.

19 20.

(Once Amended) The memory cell, as set forth in claim *16*, wherein the chalcogenide material comprises germanium selenide.

20 21.

(Once Amended) A memory cell comprising:

a first layer of dielectric material disposed over a substrate, the first layer of dielectric material having a first window therein;

a first line disposed in the first window, the first line being formed of a first conductive material that comprises one of aluminum, copper, nickel, and tungsten;

a second layer of dielectric material disposed over the first layer of dielectric material and over the first line, the second layer of dielectric material having a second window therein, the second window exposing at least a portion of the first line;

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a layer of a second conductive material disposed in the second window over the first line, the second conductive material being different from the first conductive material;

a layer of chalcogenide material disposed in the second window over the layer of the second conductive material; and

a second line formed over the layer of chalcogenide material.

26. (Once Amended) A memory cell comprising:

a first layer of dielectric material disposed over a substrate, the first layer of dielectric

material having a first window therein;

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a first line disposed in the first window, the first line being formed of a first conductive

material that comprises one of aluminum, copper, nickel, and tungsten;

a second layer of dielectric material disposed over the first layer of dielectric material and

over the first line;

a first layer of conductive material disposed over the second layer of dielectric material,

the first layer of conductive material and the second layer of dielectric material

having a second window therein, the second window exposing at least a portion of

the first line;

a layer of a second conductive material disposed in the second window over the first line,

the second conductive material being different from the first conductive material;

a layer of chalcogenide material disposed in the second window over the layer of the
second conductive material; and

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a second line formed over the layer of chalcogenide material and over the first layer of
conductive material.

28 31. (Once Amended) A memory comprising:

a memory array having a plurality of memory cells, each of the memory cells comprising:

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a first line formed over a substrate, the first line being formed of a first conductive
material that comprises one of aluminum, copper, nickel, and tungsten;

a layer of a second conductive material disposed over the first line, the second conductive
material being different from the first conductive material;

a layer of chalcogenide disposed over the layer of the second conductive material; and

a second line formed over the layer of chalcogenide.

34 38. (Once Amended) An electronic device comprising:

a processor;

a memory operatively coupled to the processor, the memory comprising a memory array
having a plurality of memory cells, each of the memory cells comprising:

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a first line formed over a substrate, the first line being formed of a first conductive
material that comprises one of aluminum, copper, nickel, and tungsten;

a layer of a second conductive material disposed over the first line, the second conductive
material being different from the first conductive material;